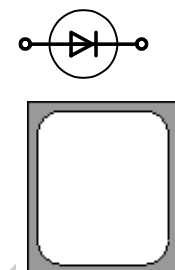


Type	Ag* Al*	V _{RRM} [V]	I _{F(AV)} [A]	Chip Size [mm] x [mm]	Package
DMHP 09	<input type="checkbox"/> Ag <input checked="" type="checkbox"/> Al	650	20	3.60 2.50	sawn on foil <input checked="" type="checkbox"/> unsawn wafer <input checked="" type="checkbox"/> * in wafer pack <input checked="" type="checkbox"/>

*Frontside options

*Please contact IXYS chip sales

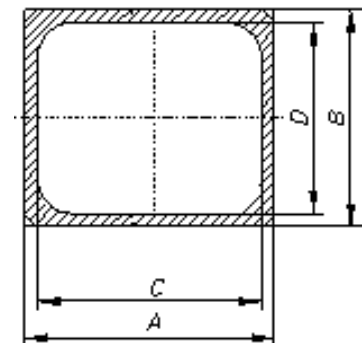
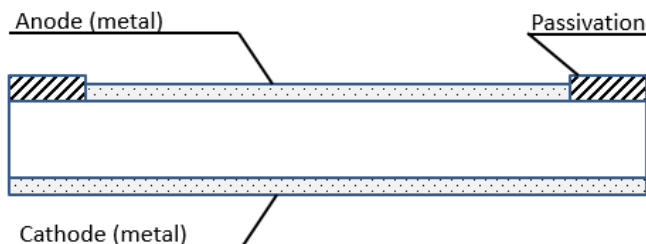


Mechanical Parameters

Area active	5.50 mm ²	Features
Area total	9.00 mm ²	
Wafer size Ø	150 mm	<ul style="list-style-type: none"> fast, soft SONIC diode low forward voltage drop small temperature coefficient low switching losses high ruggedness anode top T_{vjm} = 175°C
Thickness	290 µm	
Material	Si	
Passivation front side	Polyimide	
Metallization top side	bondable: Al	
Metallization backside	solderable (only): Al / Ti / Ni / Ag	
Recom. wire bonds (Al)	Anode Number 4	
* = stitch bonds	Ø 380 µm	
Reject Ink Dot Size	Ø 0.4-1.0 mm	
Recom. soldering temp.	< 300 °C	
Recom. Storage Environment		Applications
sawn on foil	in org. container, in dry nitrogen < 6 month	
unsawn wafer	in org. container, in dry nitrogen < 2 year	
in wafer pack	in org. container, in dry nitrogen < 2 year	
T _{stg}	-40 ... 40 °C	<ul style="list-style-type: none"> antiparallel diode for high frequency switching devices antisaturation diode snubber diode free wheeling diode in converters and motor control circuits rectifiers in switch mode power supplies (SMPS) inductive heating and melting uninterruptible power supplies (UPS) ultrasonic cleaners and welders

Dimensions

A	B	C	D
[mm]	[mm]	[mm]	[mm]
3.60	2.50	2.75	1.65



Electrical parameters

Symbol	Conditions	Ratings			
		min.	typ.	max.	
I_R	$V = V_{RRM}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$		5	50	μA
			0.1		mA
V_F	$I_F = 20\text{ A}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$		1.70	2.00	V
			1.80		V
V_{FO}	For power-loss calculations only			1.2	V
r_F	$T_{VJ} = 175^\circ\text{C}$			43.5	$\text{m}\Omega$
T_{VJ}		-55		175	$^\circ\text{C}$
$I_{F(AV)}$ *	$T_C = 80^\circ\text{C}$ DC		20		A
I_{FSM} *	$T_{VJ} = 45^\circ\text{C}$ $V = 0\text{ V}$			100	A
R_{thJC} *	DC current			2.4	K/W
Q_n	$V = 300\text{ V};$ $I_F = 20\text{ A}$ $-di_F/dt = 400\text{ A}/\mu\text{s}$ $T_{VJ} = 25^\circ\text{C}$		1		μC
I_{RM}			16		A
t_n			90		ns
E_{rec}			0.25		mJ
Q_n			2		μC
I_{RM}	$V = 300\text{ V};$ $I_F = 20\text{ A}$ $-di_F/dt = 400\text{ A}/\mu\text{s}$ $T_{VJ} = 150^\circ\text{C}$		20		A
			150		ns
			0.4		mJ

* Data according to assembled 380 μm DCB

Data according to IEC 60747

Terms of Conditions and Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of our product, please contact the sales office, which is responsible for you. Due to technical requirements our product may contain dangerous substances. For any information on the types in question please contact the sales office/partner, which is responsible for you.

Should you intend to use the product in aviation applications, in health or life endangering or life support applications, please notify. For any such applications we urgently recommend

- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures to ensure application specific product capabilities and notify that IXYS may delivery dependent on the realization of any such measures.